# 1. General description

PNP high-voltage low  $V_{CEsat}$  transistor in a SOT89 (SC-62) small and flat Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $\rm I_{C}$  and  $\rm I_{CM}$
- High collector current gain (hFE) at high IC

# 3. Applications

- LED driver for LED chain module
- LCD backlighting
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	-	-200	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-150	V
I <sub>C</sub>	collector current		-	-	-1	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C	100	220	-	

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		В
3	В	base	3 2 1 SOT89	E sym079



#### 150 V, 1 A PNP high-voltage low VCEsat transistor

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package	ackage						
	Name	Description	Version					
PBHV9115X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89					

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBHV9115X	%4G

[1] % = placeholder for manufacturing site code

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

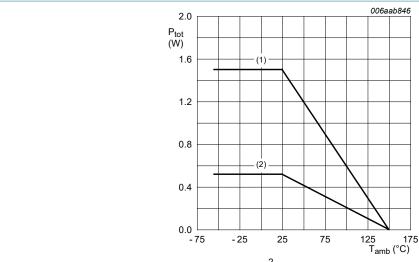
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-200	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-150	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-200	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	Α
I <sub>BM</sub>	peak base current			-	-400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	520	mW
			[2]	-	1.5	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBHV9115X

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	240	K/W
	junction to ambient		[2]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

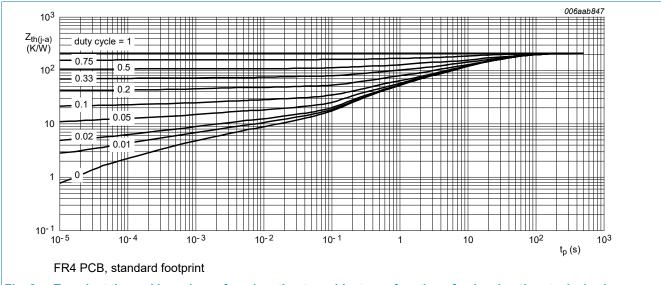
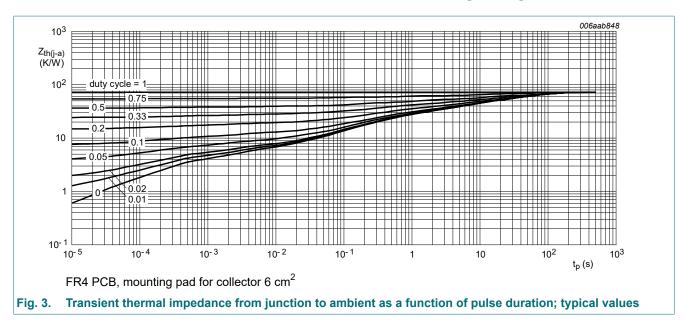


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 150 V, 1 A PNP high-voltage low VCEsat transistor



## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C	100	220	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	100	220	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	30	-	
OLSat	collector-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -10 mA; $T_{amb}$ = 25 °C	-	-60	-120	mV
		$I_C$ = -100 mA; $I_B$ = -20 mA; $T_{amb}$ = 25 °C	-	-50	-100	mV
		$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C	-	-200	-300	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-1	-1.2	V
t <sub>d</sub>	delay time	$V_{CC}$ = -6 V; $I_{C}$ = -0.5 A; $I_{Bon}$ = -0.1 A;	-	8	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C	-	282	-	ns
t <sub>on</sub>	turn-on time		-	290	-	ns
t <sub>s</sub>	storage time		-	430	-	ns
t <sub>f</sub>	fall time		-	300	-	ns
t <sub>off</sub>	turn-off time		-	730	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	115	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	10	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB}$ = -0.5 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	150	-	pF

#### 150 V, 1 A PNP high-voltage low VCEsat transistor

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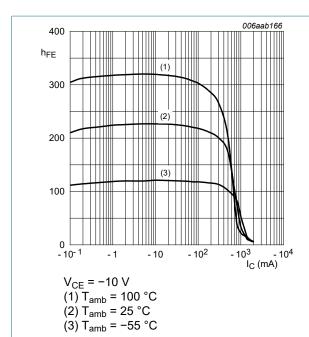


Fig. 4. DC current gain as a function of collector current; typical values

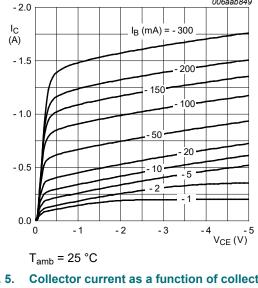


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

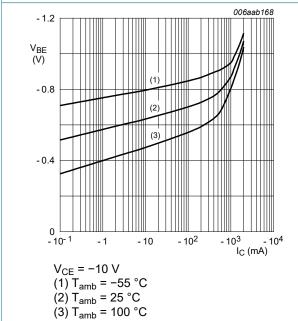
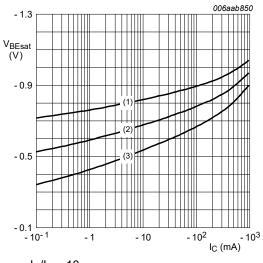


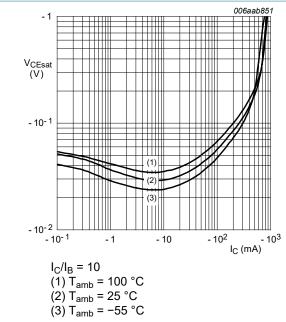
Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ (1)  $T_{amb} = -55$  °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = 100 \, ^{\circ}C$ 

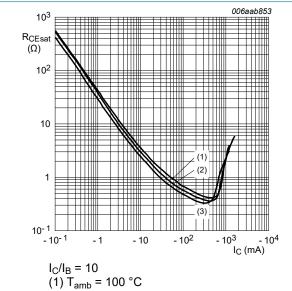
Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

#### 150 V, 1 A PNP high-voltage low VCEsat transistor



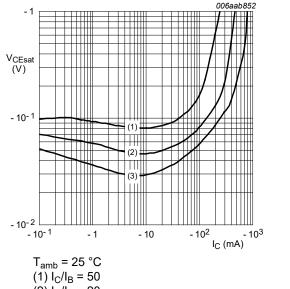
$$(3) T_{amb} = 25 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



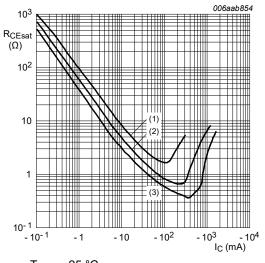
(2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -55 \, ^{\circ}C$ Fig. 10. Collector-emitter saturation resistance as a

function of collector current; typical values



(2)  $I_C/I_B = 20$ (3)  $I_C/I_B = 10$ 

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

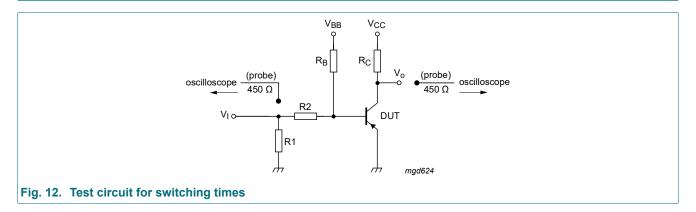


T<sub>amb</sub> = 25 °C  $(1) I_{\rm C}/I_{\rm B} = 50$  $(2) I_{\rm C}/I_{\rm B} = 20$ (3)  $I_C/I_B = 10$ 

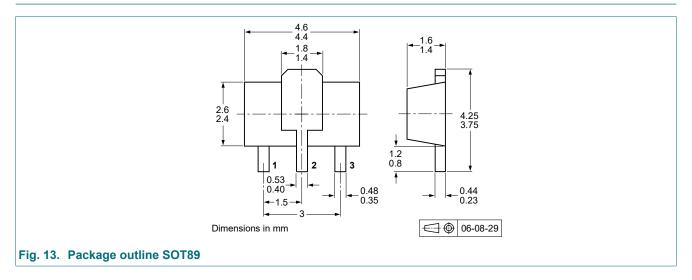
Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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# 11. Test information

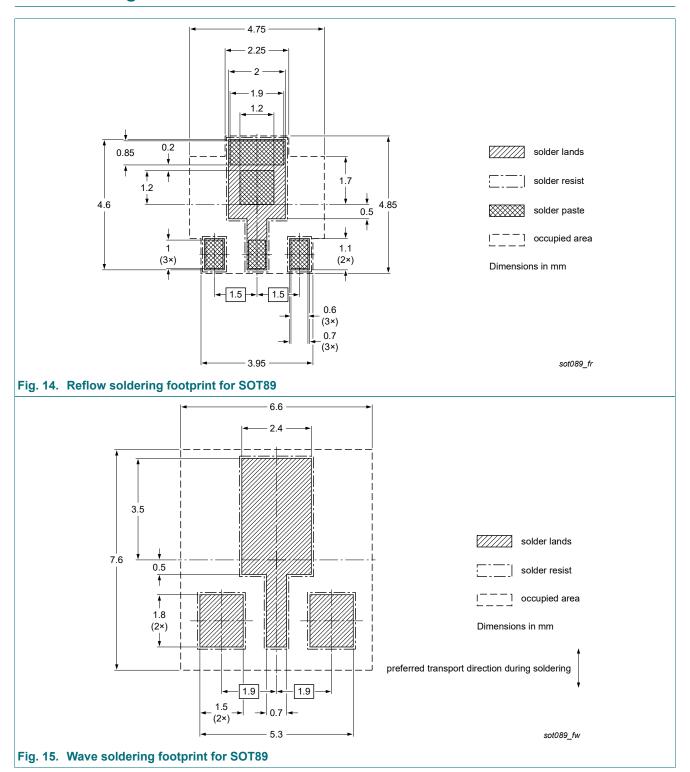


# 12. Package outline



## 150 V, 1 A PNP high-voltage low VCEsat transistor

# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Table of Novicion motory								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBHV9115X v.3	20241009	Product data sheet	-	PBHV9115X v.2				
Modifications:	<ul> <li>Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).</li> </ul>							
PBHV9115X v.2	20230717	Product data sheet	-	PBHV9115X_1				
PBHV9115X_1	20100310	Product data sheet	-	-				

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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